



30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

25 A

Features

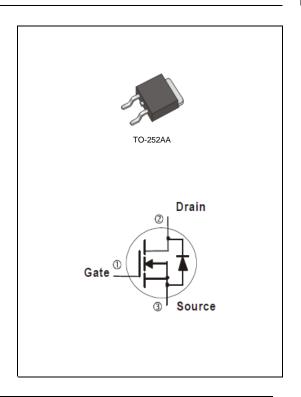
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@12A$ <25m Ω
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@6A<33m\Omega$
- · High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	25	А	
	T _C =100°C		16		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100		
Power Dissipation	T _C =25°C	Po	25	14/	
	T _C =100°C		10	W	
Continuous Drain Current	T _A =25°C	I _D	7.0		
	T _A =70°C		5.6	Α	
Power Dissipation	T _A =25°C	D-	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	32	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	5.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.2	1.7	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =12A	-	21	25	mΩ	
		V _{GS} =4.5V,I _D =6A	-	26	33		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V _{DS} =15V, I _D =8A, V _{GS} =4.5V (Note 2,3)	-	4.3	-	nC	
Gate-Source Charge	Q_gs		-	1.3	-		
Gate-Drain Charge	Q_gd		-	1.6	-		
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V, f=1.0MHZ	-	392	-	pF	
Output Capacitance	Coss		-	76	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	54	-		
Turn-On Delay Time	td _(on)	V_{DS} =15V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω (Note 2.3)	-	5.9	-	ns	
Turn-On Rise Time	t _r		-	11	-		
Turn-Off Delay Time	td _(off)		-	17	-		
Turn-Off Fall Time	t _f		-	3.8	-		
Drain-Source Diode							
Maximum Continuous Drain-Source					25	Α	
Diode Forward Current	I _S		-	-	20		
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.73	1.0	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $TJ_{(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial TJ = 25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=1mH, I_{AS} =8A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

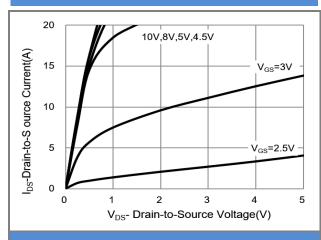


Fig.1 Output Characteristics

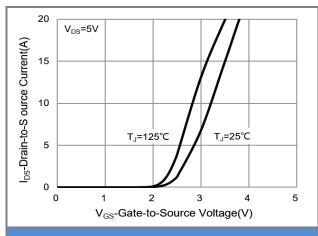


Fig.2 Transfer Characteristics

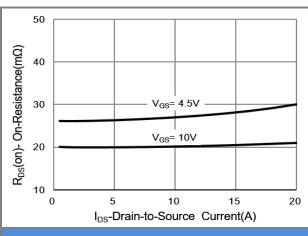


Fig.3 On-Resistance vs. Drain Current

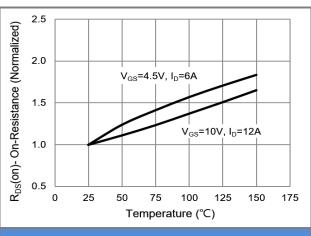
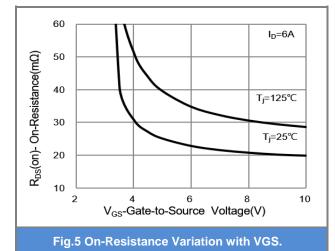


Fig.4 On-Resistance vs. Junction temperature



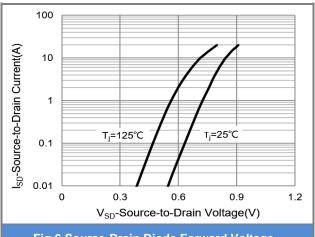


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

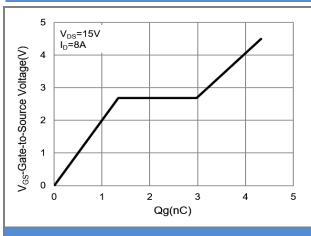


Fig.7 Gate-Charge Characteristics

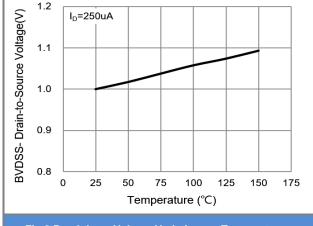


Fig.8 Breakdown Voltage Variation vs. Temperature

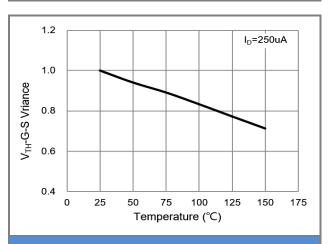


Fig.9 Threshold Voltage Variation with Temperature

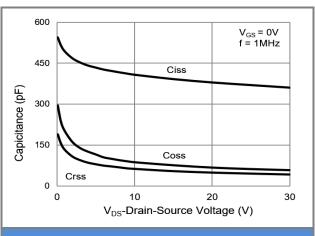
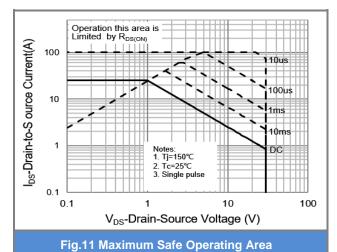


Fig.10 Capacitance vs. Drain-Source Voltage







TYPICAL CHARACTERISTIC CURVES

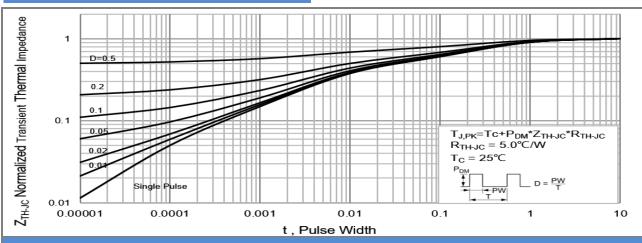
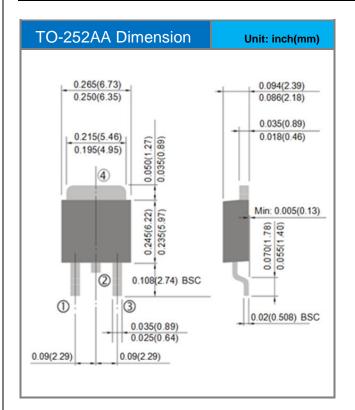


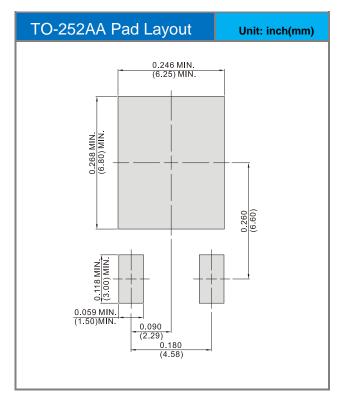
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information & Mounting Pad Layout









PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD25N03_L2_00001	TO-252AA	3,000pcs / 13" reel	D25N03	Halogen free	





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